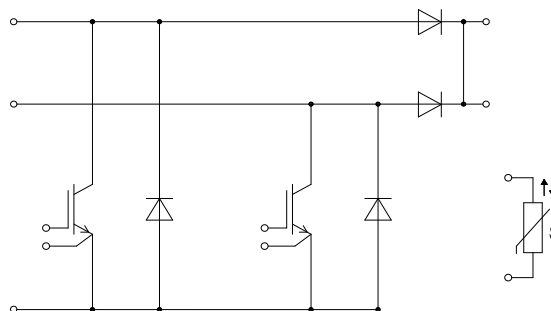
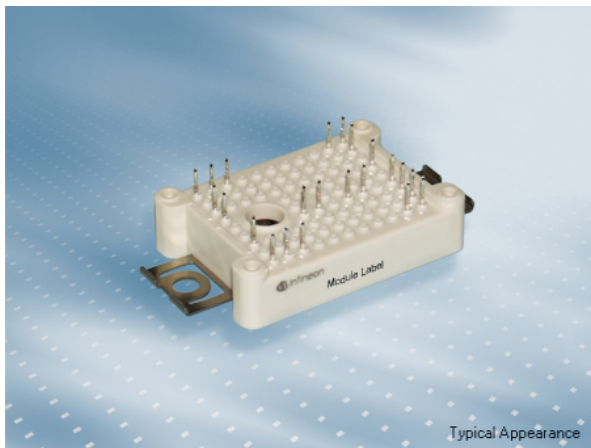


暫定データ / Preliminary Data



$V_{CES} = 1200V$
 $I_{C\ nom} = 30A / I_{CRM} = 60A$

一般応用

- ソーラーアプリケーション

Typical Applications

- Solar Applications

電気的特性

- 低スイッチング損失

Electrical Features

- Low Switching Losses

機械的特性

- 低熱インピーダンスの Al_2O_3 DCB
- 内蔵されたNTCサーミスタ
- コンパクトデザイン
- PressFIT 接合 技術

Mechanical Features

- Al_2O_3 Substrate with Low Thermal Resistance
- Integrated NTC temperature sensor
- Compact design
- PressFIT Contact Technology

Module Label Code

Barcode Code 128



Content of the Code

Digit

| | |
|----------------------------|---------|
| Module Serial Number | 1 - 5 |
| Module Material Number | 6 - 11 |
| Production Order Number | 12 - 19 |
| Datecode (Production Year) | 20 - 21 |
| Datecode (Production Week) | 22 - 23 |

DMX - Code



| | | |
|-----------------|---------------------------------|----------------------|
| prepared by: CM | date of publication: 2013-11-25 | |
| approved by: MB | revision: 2.0 | UL approved (E83335) |



暫定データ
Preliminary Data

逆極性保護diodeA / Inverse-polarity protection diode A
最大定格 / Maximum Rated Values

| | | | | |
|--|---|-------------|------------|--|
| ピーク繰返し逆電圧 Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 1200 | V |
| 最大実効順電流/chip Maximum RMS forward current per chip | $T_c = 80^{\circ}\text{C}$ | I_{FRMSM} | 50 | A |
| 整流出力の最大実効電流 Maximum RMS current at rectifier output | $T_c = 80^{\circ}\text{C}$ | I_{RMSM} | 60 | A |
| サージ順電流 Surge forward current | $t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I_{FSM} | 360 290 | A A |
| 電流二乗時間積 I^2t - value | $t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I^2t | 650 420 | A^2s A^2s |

電気的特性 / Characteristic Values

| | | | min. | typ. | max. | |
|---|---|--------------------|------|------|------|--------------------|
| 順電圧 Forward voltage | $T_{vj} = 150^{\circ}\text{C}, I_F = 30\text{ A}$ | V_F | | 0,95 | | V |
| 傾き抵抗 Slope resistance | $T_{vj} = 150^{\circ}\text{C}$ | r_T | | 0,10 | | $\text{m}\Omega$ |
| 逆電流 Reverse current | $T_{vj} = 150^{\circ}\text{C}, V_R = 1200\text{ V}$ | I_R | | 0,10 | | mA |
| ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case | /Diode (1 素子当り) / per diode | R_{thJC} | | 0,80 | 0,90 | K/W |
| ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink | /Diode (1 素子当り) / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$ | R_{thCH} | | 0,80 | | K/W |
| 動作温度 Temperature under switching conditions | | $T_{vj\text{ op}}$ | -40 | | 125 | $^{\circ}\text{C}$ |

| | |
|-----------------|---------------------------------|
| prepared by: CM | date of publication: 2013-11-25 |
| approved by: MB | revision: 2.0 |



暫定データ
Preliminary Data

IGBT、チヨッパ- / IGBT-Chopper
最大定格 / Maximum Rated Values

| | | | | |
|--|--|----------------------------|----------|--------|
| コレクタ・エミッタ間電圧 Collector-emitter voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{CES} | 1200 | V |
| 連続DCコレクタ電流 Continuous DC collector current | $T_C = 80^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ | $I_{C\text{nom}}$ I_C | 30 50 | A A |
| 繰り返しピークコレクタ電流 Repetitive peak collector current | $t_P = 1\text{ms}$ | I_{CRM} | 60 | A |
| トータル損失 Total power dissipation | $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ | P_{tot} | 375 | W |
| ゲート・エミッタ間ピーク電圧 Gate-emitter peak voltage | | V_{GES} | +/-20 | V |

電気的特性 / Characteristic Values

| | | | min. | typ. | max. | | |
|---|---|---|--------------------|------------------------|--------|-------------|---|
| コレクタ・エミッタ間飽和電圧 Collector-emitter saturation voltage | $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | $V_{CE\text{sat}}$ | 1,30 1,35 1,35 | t.b.d. | V V V | |
| ゲート・エミッタ間しきい値電圧 Gate threshold voltage | $I_C = 1,00\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$ | | V_{GEth} | 5,0 | 5,8 | 6,5 | V |
| ゲート電荷量 Gate charge | $V_{GE} = -15\text{V} \dots +15\text{V}$ | | Q_G | 0,80 | | | μC |
| 内蔵ゲート抵抗 Internal gate resistor | $T_{vj} = 25^{\circ}\text{C}$ | | R_{Gint} | 0,0 | | | Ω |
| 入力容量 Input capacitance | $f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$ | | C_{ies} | 2,00 | | | nF |
| 帰還容量 Reverse transfer capacitance | $f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$ | | C_{res} | 0,064 | | | nF |
| コレクタ・エミッタ間遮断電流 Collector-emitter cut-off current | $V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{CES} | | | 1,0 | mA |
| ゲート・エミッタ間漏れ電流 Gate-emitter leakage current | $V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{GES} | | | 100 | nA |
| ターンオン遅れ時間 (誘導負荷) Turn-on delay time, inductive load | $I_C = 30\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 4,7\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | $t_{d\text{on}}$ | 0,03 0,03 0,03 | | | μs μs μs |
| ターンオン上昇時間 (誘導負荷) Rise time, inductive load | $I_C = 30\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Gon} = 4,7\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_r | 0,01 0,01 0,01 | | | μs μs μs |
| ターンオフ遅れ時間 (誘導負荷) Turn-off delay time, inductive load | $I_C = 30\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 4,7\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | $t_{d\text{off}}$ | 0,30 0,40 0,44 | | | μs μs μs |
| ターンオフ下降時間 (誘導負荷) Fall time, inductive load | $I_C = 30\text{A}, V_{CE} = 600\text{V}$ $V_{GE} = \pm 15\text{V}$ $R_{Goff} = 4,7\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_f | 0,014 0,03 0,035 | | | μs μs μs |
| ターンオンスイッチング損失 Turn-on energy loss per pulse | $I_C = 30\text{A}, V_{CE} = 600\text{V}, L_S = 40\text{nH}$ $V_{GE} = \pm 15\text{V}, di/dt = 3000\text{A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 4,7\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{on} | 0,80 1,65 1,90 | | | mJ mJ mJ |
| ターンオフスイッチング損失 Turn-off energy loss per pulse | $I_C = 30\text{A}, V_{CE} = 600\text{V}, L_S = 40\text{nH}$ $V_{GE} = \pm 15\text{V}, du/dt = 2800\text{V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 4,7\Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{off} | 1,30 2,00 2,40 | | | mJ mJ mJ |
| 短絡電流 SC data | $V_{GE} \leq 15\text{V}, V_{CC} = 800\text{V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$ | | I_{SC} | 360 | | | A |
| ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case | IGBT部 (1素子当り) / per IGBT | | R_{thJC} | 0,35 | 0,40 | | K/W |
| ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink | IGBT部 (1素子当り) / per IGBT $\lambda_{\text{Paste}} = 1\text{W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | 0,35 | | | K/W |
| 動作温度 Temperature under switching conditions | | | $T_{vj\text{op}}$ | -40 | | 150 | $^{\circ}\text{C}$ |

| | |
|-----------------|---------------------------------|
| prepared by: CM | date of publication: 2013-11-25 |
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暫定データ
Preliminary Data

Diode-、チヨツパー / Diode-Chopper
最大定格 / Maximum Rated Values

| | | | | |
|--|--|-----------|-------------|--|
| ピーク繰返し逆電圧 Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 1200 | V |
| 連続DC電流 Continuous DC forward current | | I_F | 30 | A |
| ピーク繰返し順電流 Repetitive peak forward current | $t_P = 1 \text{ ms}$ | I_{FRM} | 30 | A |
| 電流二乗時間積 I^2t - value | $V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I^2t | 1050 985 | A^2s A^2s |

電気的特性 / Characteristic Values

| | | | min. | typ. | max. | |
|---|---|---|-------------|----------------------|--------|---|
| 順電圧 Forward voltage | $I_F = 30 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 30 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 30 \text{ A}, V_{GE} = 0 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | V_F | 1,70 1,40 1,30 | t.b.d. | V V V |
| ピーク逆回復電流 Peak reverse recovery current | $I_F = 30 \text{ A}, -di_F/dt = 3000 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | I_{RM} | 60,0 90,0 100 | | A A A |
| 逆回復電荷量 Recovered charge | $I_F = 30 \text{ A}, -di_F/dt = 3000 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | Q_r | 2,50 6,00 7,00 | | μC μC μC |
| 逆回復損失 Reverse recovery energy | $I_F = 30 \text{ A}, -di_F/dt = 3000 \text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600 \text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{rec} | 1,25 3,20 3,80 | | mJ mJ mJ |
| ジャンクション・ケース間熱抵抗 Thermal resistance, junction to case | /Diode (1 素子当り) / per diode | | R_{thJC} | 0,50 | 0,60 | K/W |
| ケース・ヒートシンク間熱抵抗 Thermal resistance, case to heatsink | /Diode (1 素子当り) / per diode $\lambda_{Paste} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | 0,55 | | K/W |
| 動作温度 Temperature under switching conditions | | | $T_{vj op}$ | -40 | 150 | $^{\circ}\text{C}$ |

NTC-サーミスタ / NTC-Thermistor

電気的特性 / Characteristic Values

| | | | min. | typ. | max. | |
|------------------------------|--|--|--------------|------|------|------------|
| 定格抵抗値 Rated resistance | $T_C = 25^{\circ}\text{C}$ | | R_{25} | 5,00 | | k Ω |
| R100の偏差 Deviation of R100 | $T_C = 100^{\circ}\text{C}, R_{100} = 493 \Omega$ | | $\Delta R/R$ | -5 | 5 | % |
| 損失 Power dissipation | $T_C = 25^{\circ}\text{C}$ | | P_{25} | | 20,0 | mW |
| B-定数 B-value | $R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$ | | $B_{25/50}$ | 3375 | | K |
| B-定数 B-value | $R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$ | | $B_{25/80}$ | 3411 | | K |
| B-定数 B-value | $R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$ | | $B_{25/100}$ | 3433 | | K |

適切なアプリケーションノートによる仕様
Specification according to the valid application note.

| | |
|-----------------|---------------------------------|
| prepared by: CM | date of publication: 2013-11-25 |
| approved by: MB | revision: 2.0 |



暫定データ
Preliminary Data

モジュール / Module

| | | | | | |
|---|--|---------------------|--------------------------------|------|------------------|
| 絶縁耐圧 Isolation test voltage | RMS, f = 50 Hz, t = 1 min. | V _{ISOL} | 2,5 | | kV |
| 内部絶縁 Internal isolation | 基礎絶縁 (クラス1, IEC 61140) basic insulation (class 1, IEC 61140) | | Al ₂ O ₃ | | |
| 沿面距離 Creepage distance | 連絡方法 - ヒートシンク / terminal to heatsink 連絡方法 - 連絡方法 / terminal to terminal | | 11,5 6,3 | | mm |
| 空間距離 Clearance | 連絡方法 - ヒートシンク / terminal to heatsink 連絡方法 - 連絡方法 / terminal to terminal | | 10,0 5,0 | | mm |
| 相対トラッキング指数 Comperative tracking index | | CTI | > 200 | | |
| | | | min. | typ. | max. |
| 内部インダクタンス Stray inductance module | | L _{sCE} | | 30 | nH |
| パワーターミナル・チップ間抵抗 Module lead resistance, terminals - chip | T _c = 25°C, /スイッチ / per switch | R _{CC+EE'} | | 5,00 | mΩ |
| 最大ジャンクション温度 Maximum junction temperature | インバータ、ブレーキチョッパー / inverter, brake-chopper 整流器 / rectifier | T _{vj max} | | | 175 °C 150 °C |
| 動作温度 Temperature under switching conditions | インバータ、ブレーキチョッパー / inverter, brake-chopper 整流器 / rectifier | T _{vj op} | -40 -40 | | 150 °C 125 °C |
| 保存温度 Storage temperature | | T _{stg} | -40 | | 125 °C |
| 質量 Weight | | G | | 24 | g |

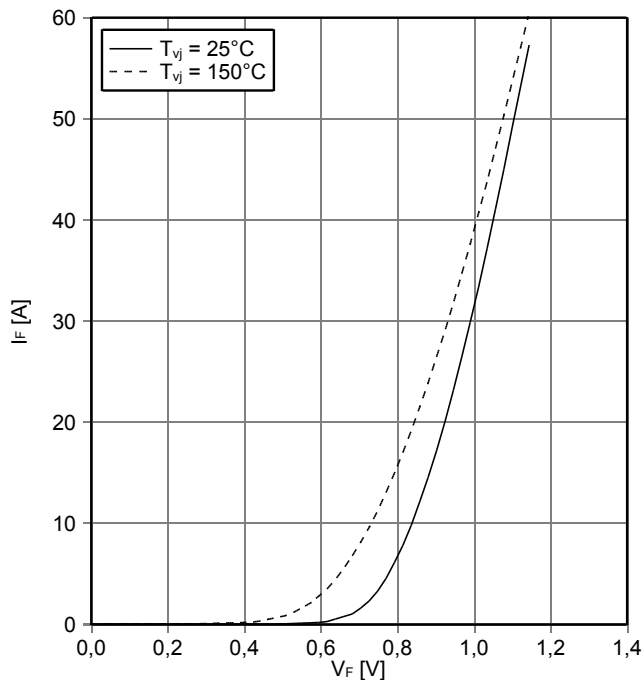
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| prepared by: CM | date of publication: 2013-11-25 |
| approved by: MB | revision: 2.0 |



暫定データ
Preliminary Data

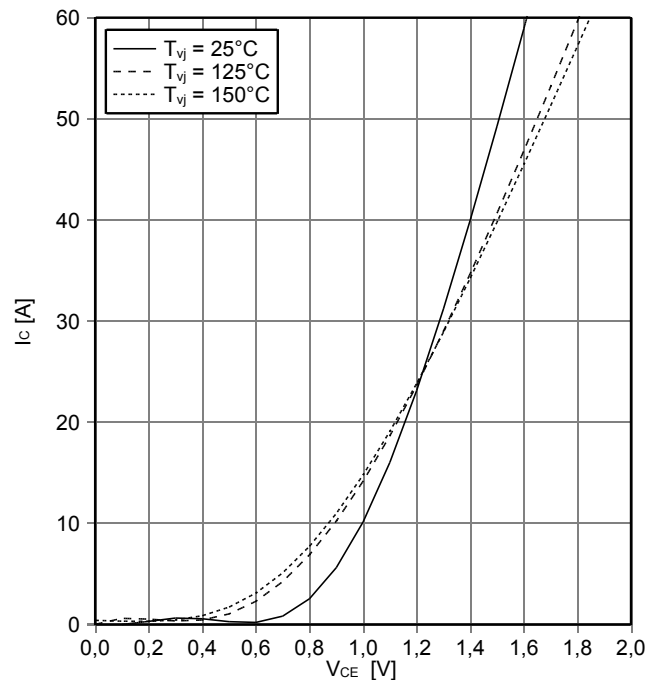
順方向特性 逆極性保護diodeA (典型)
forward characteristic of Inverse-polarity protection diode A (typical)

$I_F = f(V_F)$



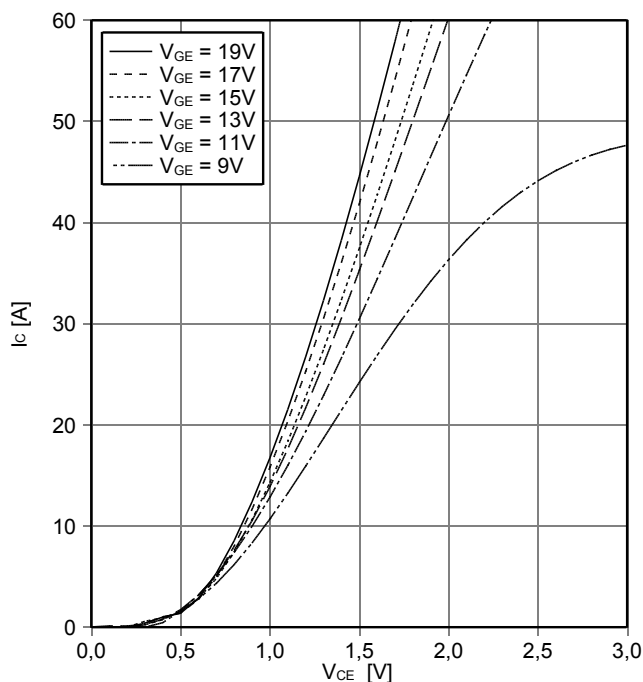
出力特性 IGBT、チヨツパー (Typical)
output characteristic IGBT-Chopper (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



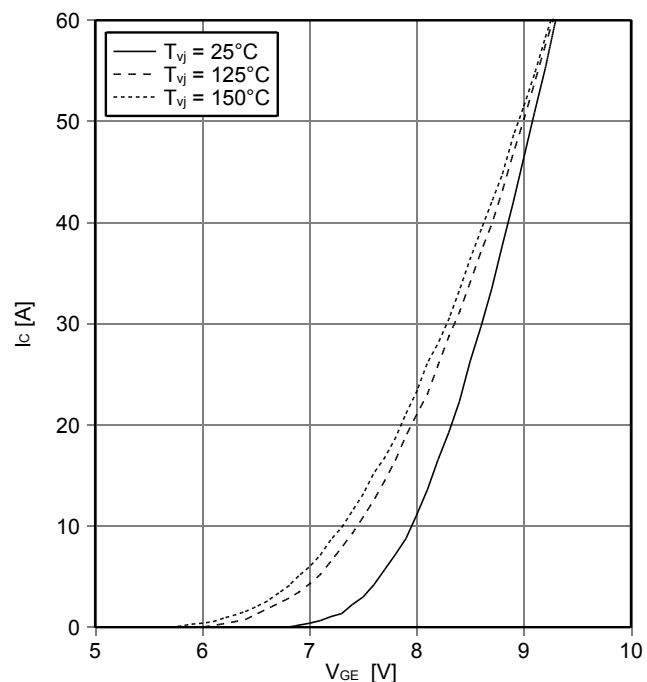
出力特性 IGBT、チヨツパー (Typical)
output characteristic IGBT-Chopper (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



伝達特性 IGBT、チヨツパー (Typical)
transfer characteristic IGBT-Chopper (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



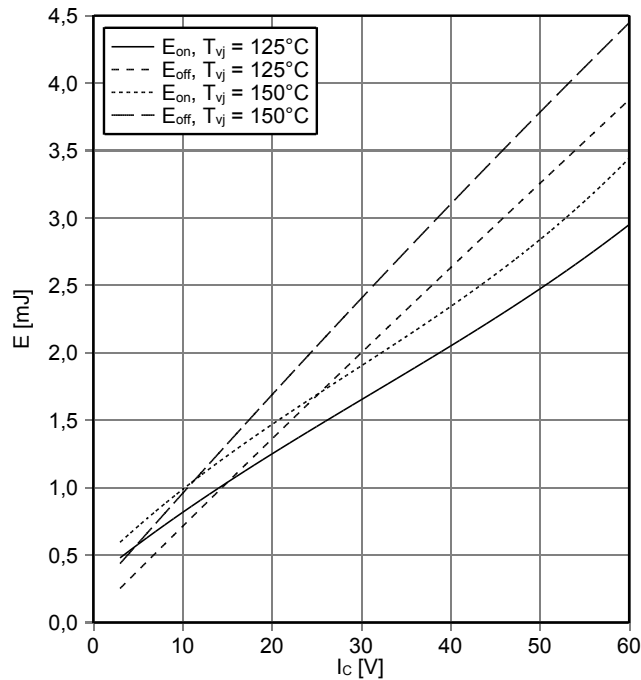
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|-----------------|---------------------------------|
| prepared by: CM | date of publication: 2013-11-25 |
| approved by: MB | revision: 2.0 |



暫定データ
Preliminary Data

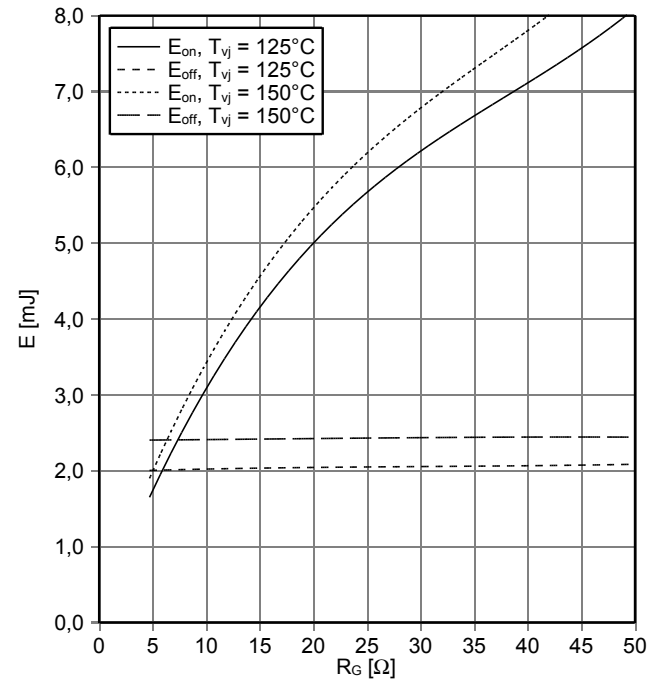
スイッチング損失 IGBT、チョッパー (Typical)
switching losses IGBT-Chopper (typical)

$E_{on} = f(I_c)$, $E_{off} = f(I_c)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 4.7\ \Omega$, $R_{Goff} = 4.7\ \Omega$, $V_{CE} = 600\text{ V}$



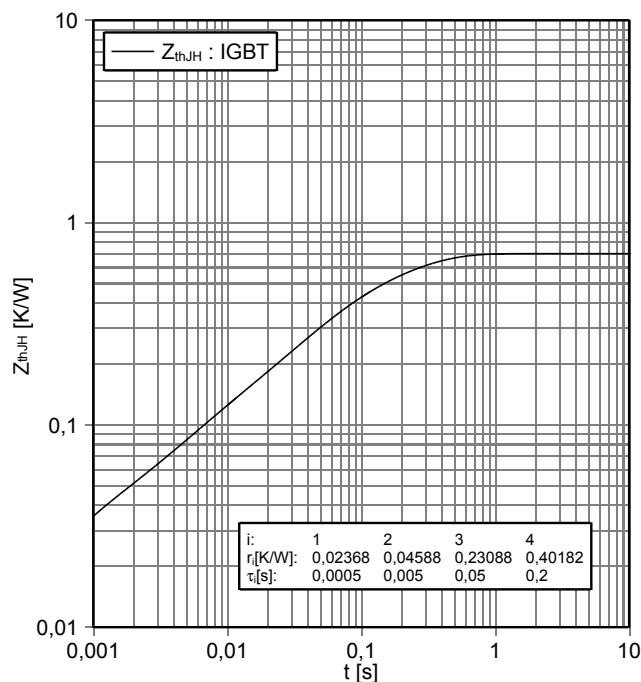
スイッチング損失 IGBT、チョッパー (Typical)
switching losses IGBT-Chopper (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_c = 30\text{ A}$, $V_{CE} = 600\text{ V}$



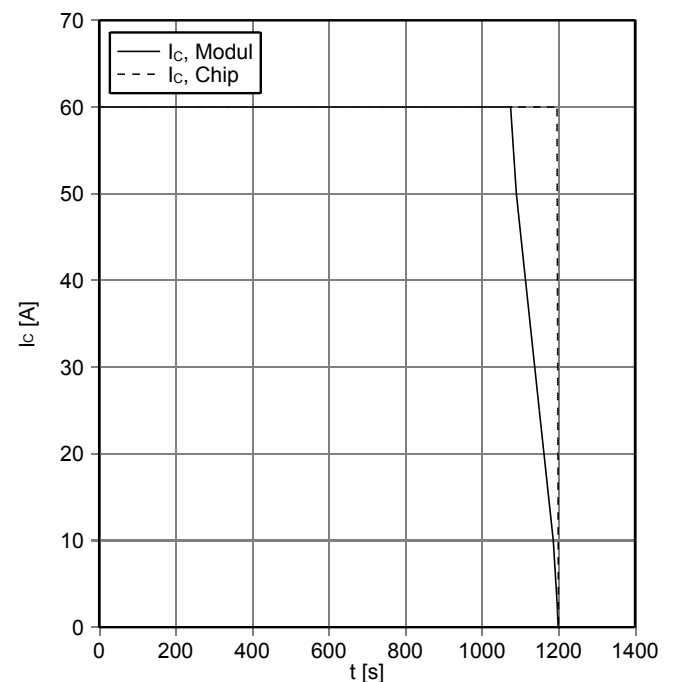
過渡熱インピーダンス IGBT、チョッパー
transient thermal impedance IGBT-Chopper

$Z_{thJH} = f(t)$



逆バイアス安全動作領域 IGBT、チョッパー (RBSOA)
reverse bias safe operating area IGBT-Chopper (RBSOA)

$I_c = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 4.7\ \Omega$, $T_{vj} = 150^\circ\text{C}$

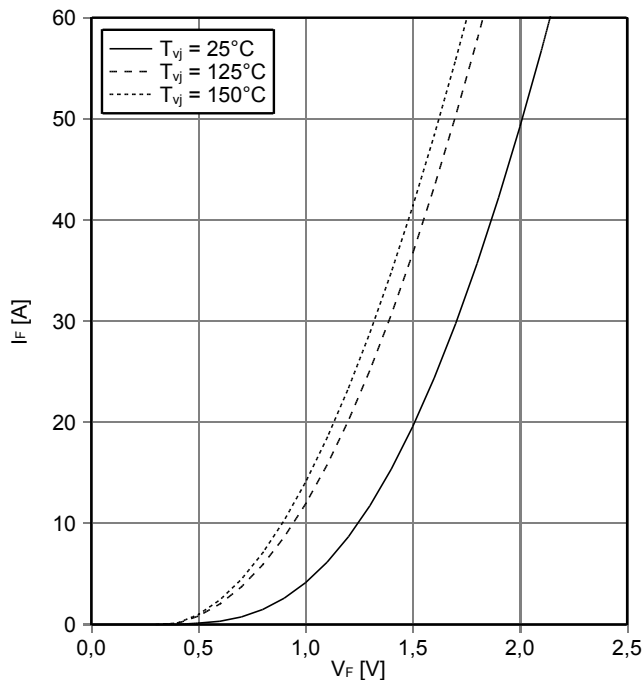


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| prepared by: CM | date of publication: 2013-11-25 |
| approved by: MB | revision: 2.0 |



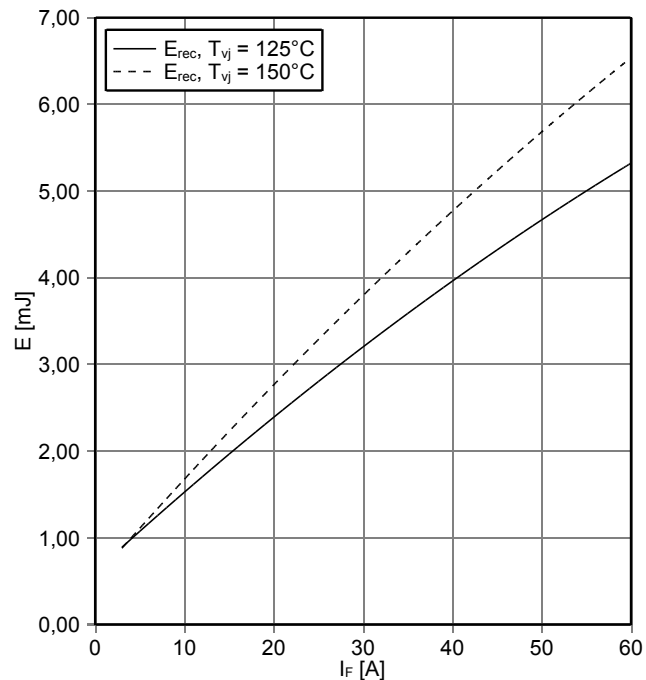
暫定データ
Preliminary Data

順電圧特性 Diode-, チョッパー (typical)
forward characteristic of Diode-Chopper (typical)
 $I_F = f(V_F)$



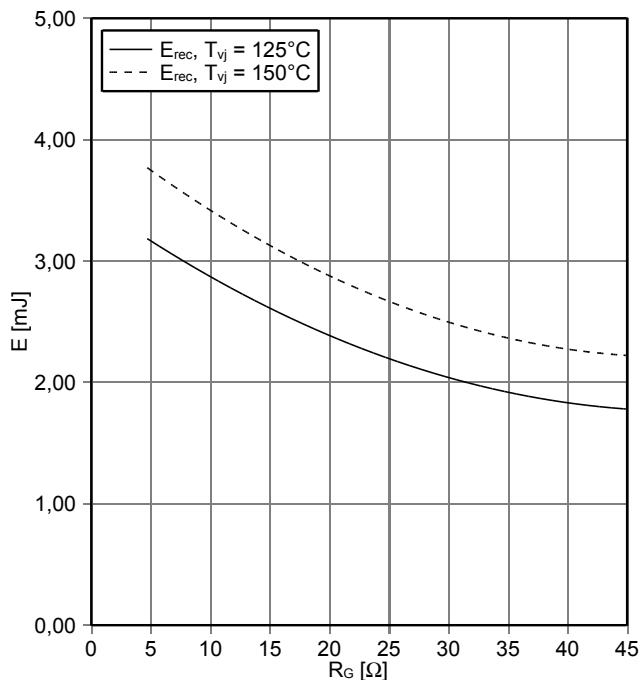
スイッチング損失 Diode-, チョッパー (Typical)
switching losses Diode-Chopper (typical)
 $E_{rec} = f(I_F)$

$R_{Gon} = 4.7 \Omega, V_{CE} = 600 V$

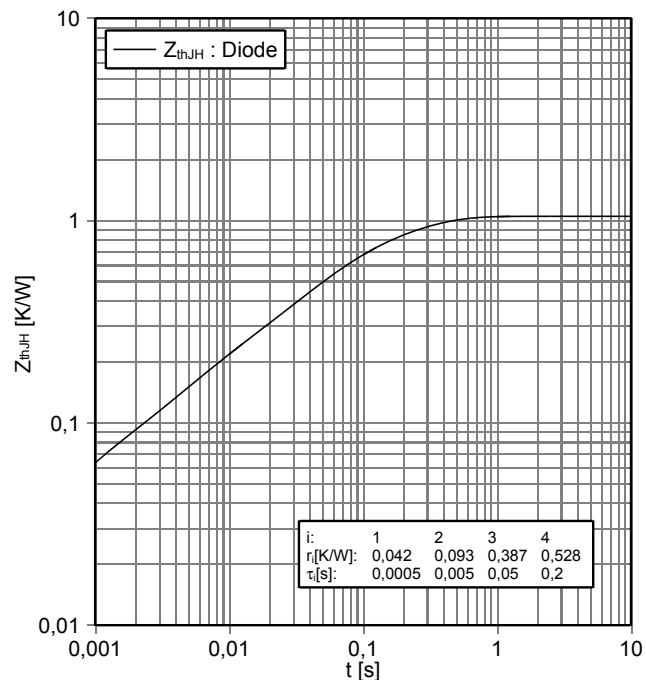


スイッチング損失 Diode-, チョッパー (Typical)
switching losses Diode-Chopper (typical)
 $E_{rec} = f(R_G)$

$I_F = 30 A, V_{CE} = 600 V$



過渡熱インピーダンス Diode-, チョッパー
transient thermal impedance Diode-Chopper
 $Z_{thJH} = f(t)$

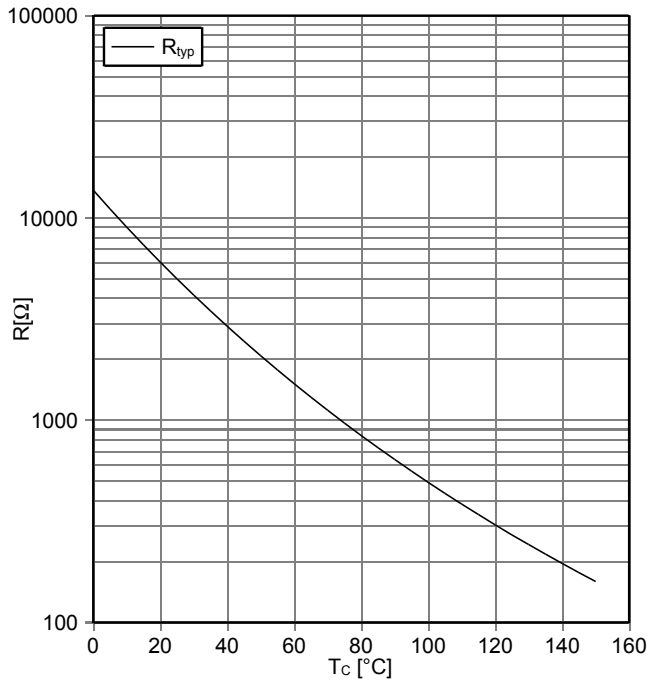


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暫定データ
Preliminary Data

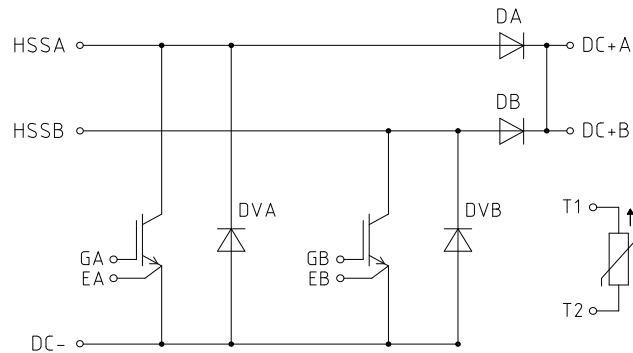
NTC-サーミスタ サーミスタの温度特性
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$



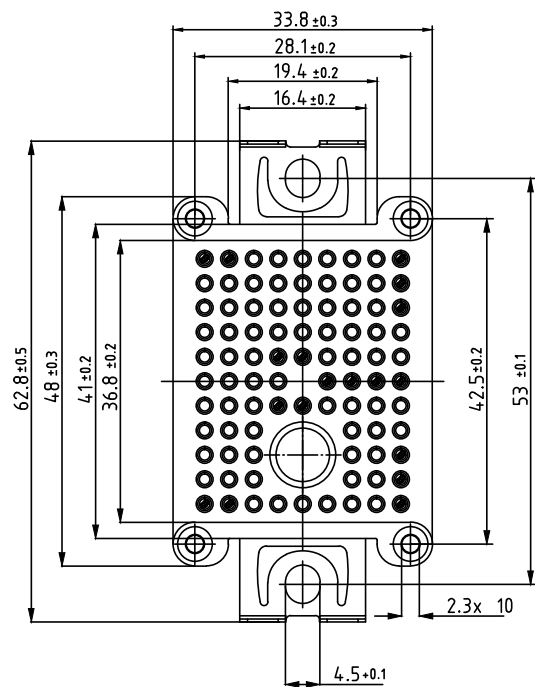
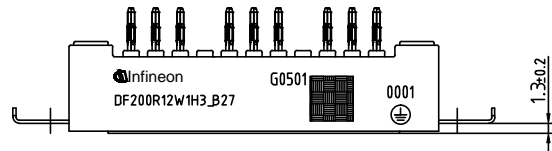
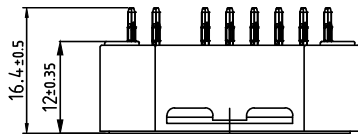
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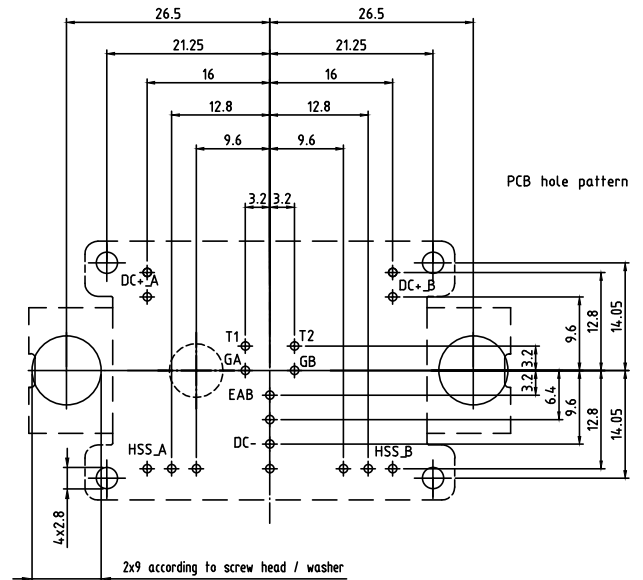
回路図 / circuit_diagram_headline



パッケージ概要 / package outlines



- Pin-Grid 3.2mm
- Tolerance of PCB hole pattern $\varnothing 0.1$
- Hole specification for contacts see AN 2009-01
- Diameters of drill $\varnothing 1.15$ mm and copper thickness in hole 25-50 μ m



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